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CLAIMS:

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- 1. A rewritable optical data storage medium (20) for high-speed recording by means of a focused radiation beam (10), said medium comprising a substrate (7) carrying a stack (2) of layers, which stack comprises, a substantially transparent first auxiliary layer I1 (3), a substantially transparent second auxiliary layer I2 (5) having a thickness d_{I2} , and a recording layer (4) of a phase-change material comprising a composition $Ge_xSn_ySb_{1-x-y}$, where 0.05 < x < 0.30 and 0.15 < y < 0.30, which recording layer is interposed between I1 and I2, and a third auxiliary layer I3 (6) with a thickness d_{I3} acting as a heat sink and being present at a side of I2 opposite to the side of the recording layer, characterized in that $\lambda_{I2}/d_{I2} > 5*10^8$ W m⁻² K⁻¹, in which formula λ_{I2} is the heat conduction coefficient of the material of the I2 layer.
- 2. An optical data storage medium (20) as claimed in Claim 1, wherein the second auxiliary layer 12 mainly comprises $(ZnS)_{80}(SiO_2)_{20}$ and $d_{12} < 10$ nm.
- 15 3. An optical data storage medium (20) as claimed in Claim 1, wherein the second auxiliary layer I2 comprises at least one selected from the group of Ge₃N₄, Si₃N₄, Al₂O₃, Hf_xN_y, ITO (In₂O₃:Sn) and Ta₂O₅.
- 4. An optical data storage medium (20) as claimed in any one of Claims 1, 2 or 3,
 20 wherein the recording layer (4) has a thickness d_P and d_P is smaller than 15 nm.
 - 5. An optical data storage medium (20) as claimed in any one of Claims 1, 2, 3 or 4, wherein the recording layer additionally comprises at least one selected from In, Ag or Cu.
- 25 6. An optical data storage medium (20) as claimed in Claim 5, wherein the at least one is present in a concentration up to 10 at.%.

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- 7. An optical data storage medium (20) as claimed in Claim 1, wherein the third auxiliary layer I3 mainly comprises Ag.
- 8. An optical data storage medium (20) as claimed in Claim 7, wherein the thickness d_{I3} of the third auxiliary layer 13 is at least 150 nm.

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- 9. An optical data storage medium (20) as claimed in any one of Claims 1 to 8, wherein a substantially transparent fourth auxiliary layer I4 (8) is present between the third auxiliary layer I3 (6) and the second auxiliary layer I2 (5) screening the third auxiliary layer I3 from a chemical influence of the second auxiliary layer I2.
- 10. An optical data storage medium as claimed in Claim 9, wherein the fourth auxiliary layer I4 (8) comprises at least one of Si_3N_4 or Ge_3N_4 .
- 15 11. An optical data storage medium as claimed in Claim 10, wherein the fourth auxiliary layer I4 has a thickness $d_H \le 3$ nm.
 - 12. Use of an optical data storage medium (20) according to any one of the preceding Claims for high speed recording with a recording speed of at least 35 m/s.